



DUAL P-CHANNEL 60V ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Package	I _D T _A = +25°C (Notes 4 & 6)
-60V	85mΩ @ V _{GS} = -10V	SO-8	-3.9A
-00 V	125mΩ @ V _{GS} = -4.5V	30-6	-3.2A

Description

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

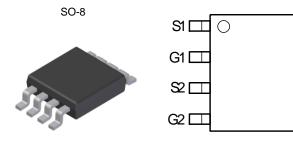
- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

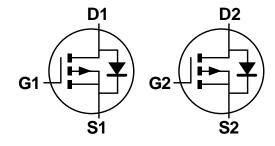
Features

- Low On-Resistance
- · Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Low Profile SOIC Package
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMP6A16DN8Q)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.074 grams (Approximate)





Top View Top View Equivalent Circuit

oxdot D1

oxdot D1

 \Box D2

 \Box D2

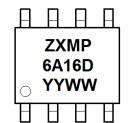
Ordering Information (Note 4)

Part Number	Case	Packaging
ZXMP6A16DN8TA	SO-8	500/Tape & Reel
ZXMP6A16DN8TC	SO-8	2,500/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP6A16D = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 16 = 2016) WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-60	V
Gate-Source Voltage		(Note 5)	V_{GS}	±20	V
		(Notes 7 & 9)	Ι _D	-3.9	
Continuous Drain Current	V _{GS} = 10V	$T_A = +70^{\circ}C$ (Notes 7 & 9)		-3.1	Α
		(Notes 6 & 9)		-2.9	
Pulsed Drain Current		(Notes 8 & 9)	I _{DM}	-18.3	Α
Continuous Source Current (Bod	y Diode)	(Notes 7 & 9)	Is	-3.2	Α
Pulsed Source Current (Body Did	ode)	(Notes 8 & 9)	I _{SM}	-18.3	А

Thermal Characteristics

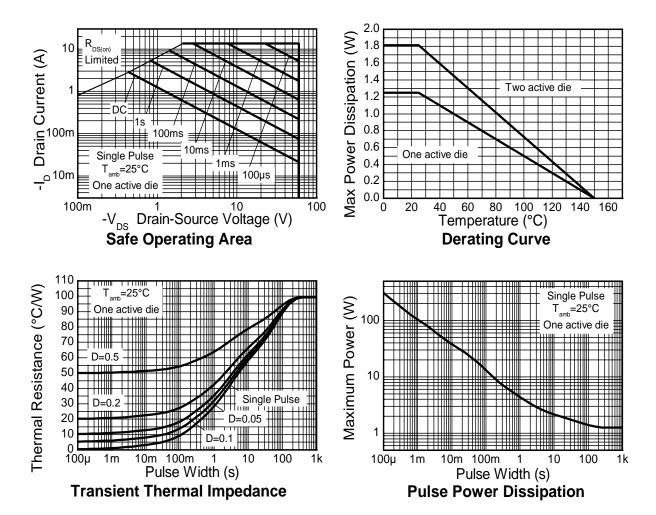
Characteristic	Symbol	Value	Unit	
	(Notes 6 & 9)	P _D	1.25 10.0	
Power Dissipation Linear Derating Factor	(Notes 6 & 10)		1.81 14.5	W mW/°C
	(Notes 7 & 9)		2.15 17	
	(Notes 6 & 9)		100	
Thermal Resistance, Junction to Ambient	(Notes 6 & 10)	$R_{ heta JA}$	70	0000
	(Notes 7 & 9)		60	°C/W
Thermal Resistance, Junction to Lead	(Notes 9 & 11)	$R_{ heta JL}$	48.85	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

Notes:

- 5. AEC-Q101 VGS maximum is ± 16 V.
- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note (5), except the device is measured at $t \le 10$ sec. 8. Same as Note (5), except the device is pulsed with D = 0.02 and pulse width 300 μ s.
- 9. For a dual device with one active die.
- 10. For a device with two active die running at equal power.
 11. Thermal resistance from junction to solder-point.



Thermal Characteristics (Continued)





Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

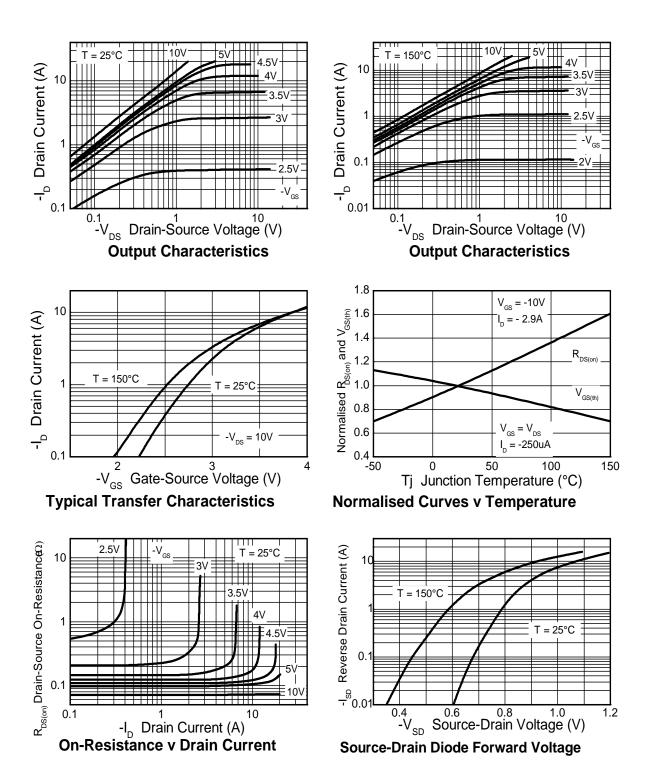
Characteristic	Symbol	Min	Тур	Max	Unit	Test Co	ondition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-60	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1.0	μΑ	$V_{DS} = -60V, V_{GS}$	= 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS	•			•		•	
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	_	V	$I_D = -250 \mu A, V_{DS} = V_{GS}$	
Chatia Dunin Course On Benintanna (Neta 40)			_	85	0	$V_{GS} = -10V, I_{D} =$	-2.9A
Static Drain-Source On-Resistance (Note 12)	R _{DS(ON)}	_	_	125	mΩ	$V_{GS} = -4.5V, I_{D} =$: -2.4A
Forward Transconductance (Notes 12 & 13)	g FS	_	7.2	_	S	$V_{DS} = -15V, I_{D} =$	-2.9A
Diode Forward Voltage (Note 12)	V _{SD}	_	-0.85	-0.95	V	I _S = -3.4A, V _{GS} =	0V, T _J = +25°C
Reverse Recovery Time (Note 13)	t _{RR}	_	29.2	_	ns	$I_S = -2A$, di/dt = 100A/ μ s,	
Reverse Recovery Charge (Note 13)	Q_{RR}	_	39.6	_	nC	T _J = +25°C	
DYNAMIC CHARACTERISTICS (Note 14)	•			•		•	
Input Capacitance	C _{ISS}	_	1,021	_	pF	.,	
Output Capacitance	Coss	_	83.1	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ -f = 1MHz	
Reverse Transfer Capacitance	C _{RSS}	_	56.4	_	pF	1 = 1101112	
Total Gate Charge	Q_G	_	12.1	_	nC	$V_{GS} = -5V$	
Total Gate Charge	Q_{G}	_	24.2	_	nC		$V_{DS} = -30V$,
Gate-Source Charge	Q_{GS}	_	2.5	_	nC	$V_{GS} = -10V$	$I_D = -2.9A$
Gate-Drain Charge	Q_GD	_	3.7	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	3.5	_	ns		
Turn-On Rise Time	t _R	_	4.1	_	ns	$V_{DD} = -30V, V_{GS} = -10V,$ $I_{D} = -1A, R_{G} \cong 6.0\Omega$	
Turn-Off Delay Time	t _{D(OFF)}	_	35	_	ns		
Turn-Off Fall Time	t _F	_	10	_	ns		

Notes:

- 12. Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
 13. For design aid only, not subject to production testing.
 14. Switching characteristics are independent of operating junction temperatures.

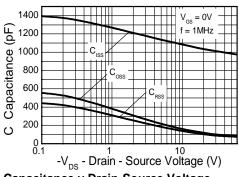


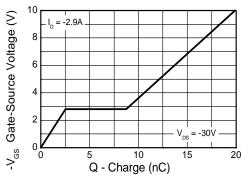
Typical Characteristics





Typical Characteristics (Continued)

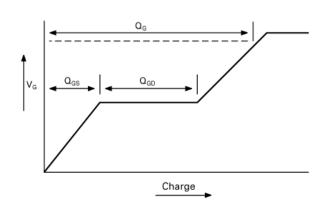


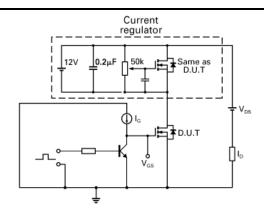


Capacitance v Drain-Source Voltage

Gate-Source Voltage v Gate Charge

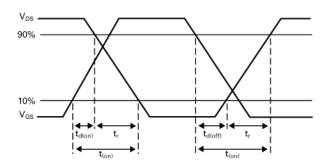
Test Circuits

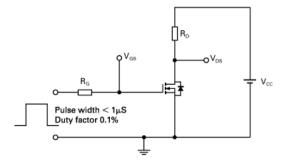




Basic gate charge waveform

Gate charge test circuit





Switching time waveforms

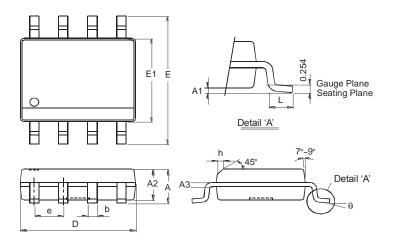
Switching time test circuit



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

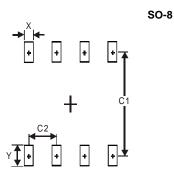




SO-8				
Dim	Min	Max		
Α	-	1.75		
A1	0.10	0.20		
A2	1.30	1.50		
A3	0.15	0.25		
b	0.3	0.5		
D	4.85	4.95		
Е	5.90	6.10		
E1	3.85	3.95		
е	1.27 Typ			
h	-	0.35		
L	0.62	0.82		
θ	0°	8°		
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1 27



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